

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	392	((porous rough\$4 pore porosity) same (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source)) and "313"/\$.ccls. and cathode and anode	US-PGPUB; USPAT	OR	ON	2005/05/17 16:05
L2	242	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source)) and "313"/\$.ccls. and cathode and anode	US-PGPUB; USPAT	OR	ON	2005/05/17 16:05
L3	287	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source)) and "313"/\$.ccls. and (etch\$3 remov\$3)	US-PGPUB; USPAT	OR	ON	2005/05/17 17:04
L4	57	("3735186" "3755704" "4652467" "4940916" "4987101" "5103288" "5194780" "5225820" "5393712").PN. OR ("5525857").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:15
L5	56	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source)) and (etch\$3 remov\$3)	EPO; JPO; DERWENT	OR	ON	2005/05/17 16:21
L6	302	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source))	EPO; JPO; DERWENT	OR	ON	2005/05/17 16:22
L7	180	((porous rough\$4 pore porosity) near3 (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source))	EPO; JPO; DERWENT	OR	ON	2005/05/17 16:38
L8	1	"6835111".pn.	EPO; JPO; DERWENT	OR	ON	2005/05/17 16:40
L9	1	"6835111".pn.	US-PGPUB; USPAT	OR	ON	2005/05/17 16:40

L10	42	("3665241" "3755704" "3812559" "3954523" "4016017" "4266233" "4652467" "4857161" "4987101" "5103288" "5142184" "5186670" "5194780" "5229331" "5259799" "5358908" "5372973" "5430300" "5458518" "5470801" "5473222" "5483067" "5529524" "5569058" "5578896" "5585301" "5597444" "5653619" "5663608" "5684356" "5712534" "5793154" "5804910" "5853492" "5869169" "5898258" "6028322" "6232705" "6251470" "6255156" "6277765" "6333215").PN. OR ("6835111").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:40
L11	12	("3998678" "4410832" "4663559" "4835438" "4990766" "5012153" "5136205" "5189341" "5256936").PN. OR ("5793154").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:42
L12	146	("3475664" "3506506" "3531857" "3665241" "3700510" "3755704").PN. OR ("3998678").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:50
L13	67	("3755704" "3789471" "3812559" "3894332" "3921022" "3998678" "4008412" "4178531" "4307507" "4513308" "4536942" "4578614" "4685996" "4721885" "4827177" "4874981" "4970887" "4975382").PN. OR ("5007873").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:48
L14	15	(("3755704" "3789471" "3812559" "3894332" "3921022" "3998678" "4008412" "4178531" "4307507" "4513308" "4536942" "4578614" "4685996" "4721885" "4827177" "4874981" "4970887" "4975382").PN. OR ("5007873").URPN.) and (pore porosity porous rough\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:48

L15	27	(("3475664" "3506506" "3531857" "3665241" "3700510" "3755704").PN. OR ("3998678").URPN.) and (pore porosity porous rough\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2005/05/17 16:51
L16	987	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source)) and "438"/\$.ccls. and (etch\$3 remov\$3)	US-PGPUB; USPAT	OR	ON	2005/05/17 17:04
L17	110	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron field) with (emission emitting emissive source)) and "445"/\$.ccls. and (etch\$3 remov\$3)	US-PGPUB; USPAT	OR	ON	2005/05/17 17:05
L18	1081	16:17	US-PGPUB; USPAT	OR	ON	2005/05/17 17:04
L19	485	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and ((electron) with (emission emitting emissive source)) and "438"/\$.ccls. and (etch\$3 remov\$3)	US-PGPUB; USPAT	OR	ON	2005/05/17 17:04
L20	579	19:17	US-PGPUB; USPAT	OR	ON	2005/05/17 17:05
L21	244	((porous rough\$4 pore porosity) with (SiO silicon insulat\$3 isolat\$3 dielectric)) and (electron near3 (emission emitting emissive source)) and ("438"/\$.ccls. "445"/\$.ccls.) and ((etch\$3 remov\$3) same (SiO silicon insulat\$3 isolat\$3 dielectric))	US-PGPUB; USPAT	OR	ON	2005/05/17 17:07